Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

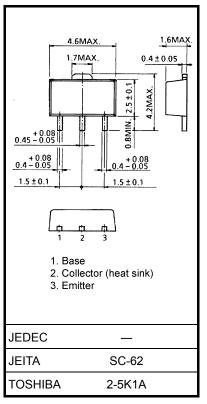
# 2SC2873

# Power Amplifier Applications Power Switching Applications

- Low saturation voltage:  $V_{CE}$  (sat) = 0.5 V (max) (IC = 1 A)
- High-speed switching time:  $t_{stg} = 1.0 \mu s$  (typ.)
- Small flat package
- Pc = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SA1213

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	$V_{CBO}$	50	V	
Collector-emitter voltage	V <sub>CEO</sub>	50	V	
Emitter-base voltage	V <sub>EBO</sub>	5	V	
Collector current	IC	2	Α	
Base current	ΙΒ	0.4	Α	
	PC	500	mW	
Collector power dissipation	PC	1000		
	(Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T <sub>stg</sub>	−55 to 150	°C	



Weight: 0.05 g (typ.)

- Note 1: Mounted on a ceramic substrate (250 mm<sup>2</sup> × 0.8 t)
- Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

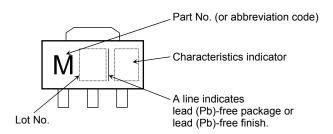
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

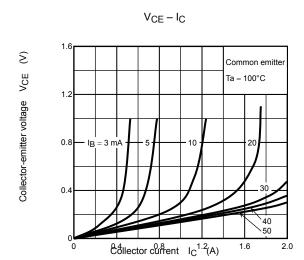
## Electrical Characteristics (Ta = 25°C)

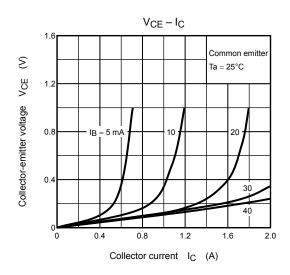
Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off cu	urrent	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	_	0.1	μA
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	_	_	0.1	μΑ
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note 3)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	70	_	240	_
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 2.0 A	20	_	_	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 A	_	_	0.5	٧
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 A	_	_	1.2	V
Transition frequency		f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	_	120	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	30	_	pF
Switching time	Turn-on time	t <sub>on</sub>	OUTPUT  20 µs INPUT  B1   C   C   C   C   C   C   C   C   C	_	0.1	_	
	Storage time	t <sub>stg</sub>		_	1.0	_	μs
	Fall time	t <sub>f</sub>	I <sub>B1</sub> = -I <sub>B2</sub> = 0.05 A, DUTY CYCLE ≤ 1%	_	0.1	_	

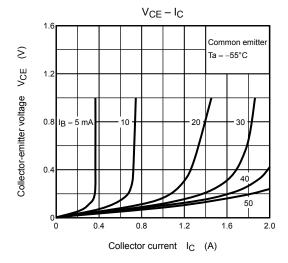
Note 3:  $h_{FE(1)}$  classification O: 70 to 140, Y: 120 to 240

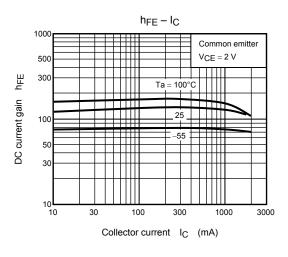
### Marking

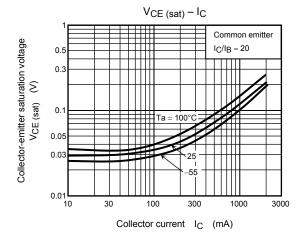


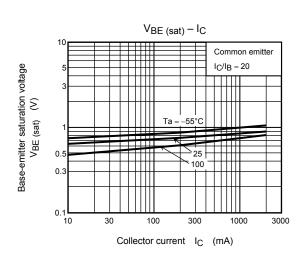


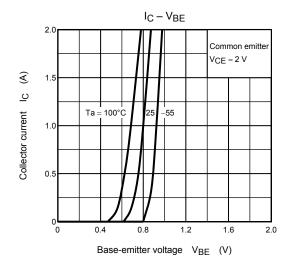


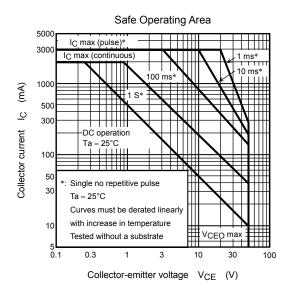


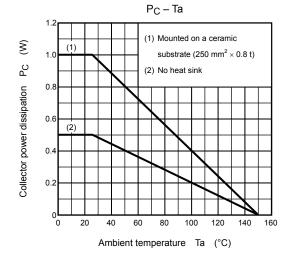












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